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NTE2673 (NPN) & NTE2674 (PNP)
Silicon Complementary Transistors
General Purpose Power
TO220FP Type Package

Features:

- Low Collector–Emitter Saturation Voltage: $V_{CD(sat)}$ = 0.5V Typ (I_C/I_B = 2A/0.2A)

Absolute Maximum Ratings: (T_A = +25°C unless otherwise specified)

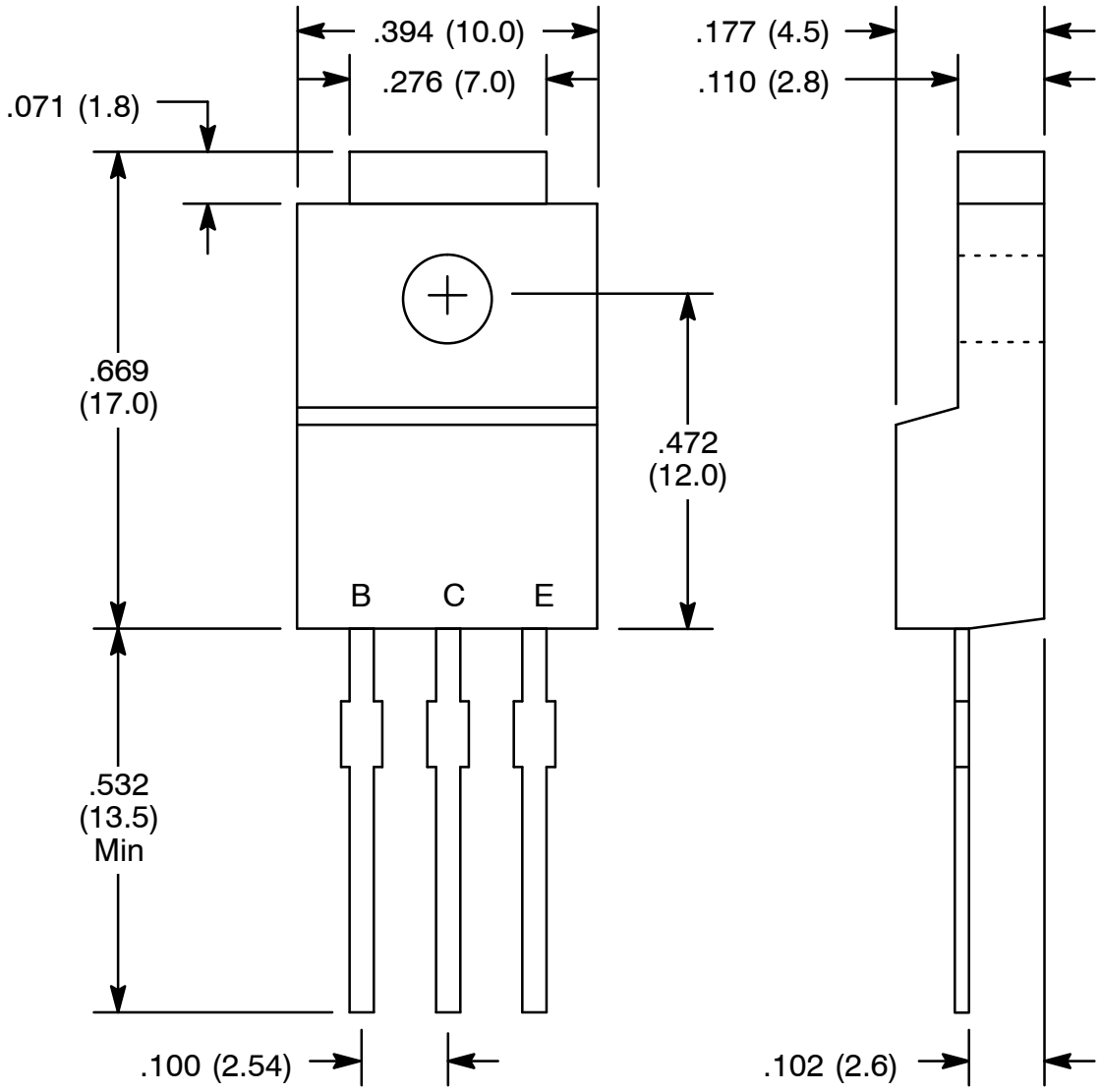
Collector–Base Voltage, V_{CBO} 60V
Collector–Emitter Voltage, V_{CEO} 50V
Emitter–Base Voltage, V_{EBO} 5V
Collector Current, I_C
  Continuous 3A
  Peak (Note 1) 4.5A
Collector Power Dissipation (T_C = +25°C, Note 2), P_D 25W
Operating Junction Temperature, T_J . . . . . +150°C
Storage Temperature Range, T_{stg} . . . . . –55° to +150°C

Note 1. Single pulse: Pulse Width = 10ms.
Note 2. Printed circuit board 1.7mm thick, collector copper plating 1cm^2 or larger.

Electrical Characteristics: (T_A = +25°C unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector–Base Breakdown Voltage	$V_{(BR)CBO}$	I_C = 50μA	60	–	–	V
Collector–Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C = 1mA	50	–	–	V
Emitter–Base Breakdown Voltage	$V_{(BR)EBO}$	I_E = 50μA	5	–	–	V
Collector Cutoff Current	I_{CBO}	V_{CE} = 40V	–	–	1	μA
Emitter Cutoff Current	I_{EBO}	V_{EB} = 4V	–	–	1	μA
Collector–Emitter Saturation Voltage	$V_{CE(sat)}$	I_C = 2A, I_B = 200mA, Note 3	–	0.5	1.0	V
DC Current Transfer Ratio	h_{FE}	I_C = 500mA, V_{CE} = 3V, Note 3	60	–	320	
Transition Frequency	f_T	I_E = -500mA, V_{CE} = 5V, f = 30MHz, Note 3	–	90	–	MHz
Output Capacitance	C_{ob}	V_{CB} = 10V, I_E = 0A, f_{test} = 1MHz	–	40	–	pF

Note 3. Measured using pulse current.


.394 (10.0)
.276 (7.0)
.071 (1.8)
.669
(17.0)
.472
(12.0)
B
C
E
.532
(13.5)
Min
.100 (2.54)
.177 (4.5)
.110 (2.8)
.102 (2.6)